

Features

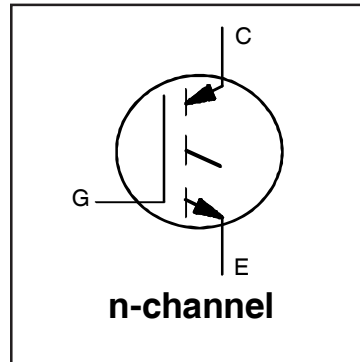
- Low $V_{CE(on)}$ Planar IGBT Technology
- Low Switching Losses
- Square RBSOA
- 100% of The Parts Tested for I_{LM} ①
- Positive $V_{CE(on)}$ Temperature Coefficient.
- Lead-Free, RoHS Compliant
- Automotive Qualified *

Benefits

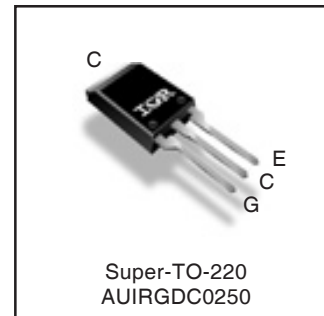
- Device optimized for soft switching applications
- High Efficiency due to Low $V_{CE(on)}$, low switching losses
- Rugged transient performance for increased reliability
- Excellent current sharing in parallel operation
- Low EMI

Application

- PTC Heater
- Relay Replacement



$V_{CES} = 1200V$
 $I_C = 81A @ T_C = 100^\circ C$
 $V_{CE(on)} \text{ typ.} = 1.37V @ 33A$



G	C	E
Gate	Collector	Emitter

Base part number	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRGDC0250	Super-TO-220	Tube	50	AUIRGDC0250

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is $25^\circ C$, unless otherwise specified.

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	1200	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	141 ⑤	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	81	
I_{CM}	Pulse Collector Current, $V_{GE} = 15V$ ②	99	
I_{LM}	Clamped Inductive Load Current, $V_{GE} = 20V$ ①	99	V
V_{GE}	Continuous Gate-to-Emitter Voltage	± 20	
	Transient Gate-to-Emitter Voltage	± 30	
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	543	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	217	
T_J	Operating Junction and	-55 to +150	$^\circ C$
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec. (1.6mm from case)	300	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$ (IGBT)	Thermal Resistance Junction-to-Case (IGBT) ③	—	—	0.23	$^\circ C/W$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink (flat, greased surface)	—	0.50	—	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	—	62	—	

*Qualification standards can be found at <http://www.irf.com/>

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)CES}	Collector-to-Emitter Breakdown Voltage	1200	—	—	V	V _{GE} = 0V, I _C = 250μA ③
ΔV _{(BR)CES} /ΔT _J	Temperature Coeff. of Breakdown Voltage	—	1.2	—	V/°C	V _{GE} = 0V, I _C = 1mA (25°C-150°C) ③
V _{CE(on)}	Collector-to-Emitter Saturation Voltage	—	1.37	1.57	V	I _C = 33A, V _{GE} = 15V, T _J = 25°C
		—	1.45	—		I _C = 33A, V _{GE} = 15V, T _J = 150°C
V _{GE(th)}	Gate Threshold Voltage	3.0	—	6.0	V	V _{CE} = V _{GE} , I _C = 250μA
ΔV _{GE(th)} /ΔT _J	Threshold Voltage temp. coefficient	—	-15	—	mV/°C	V _{CE} = V _{GE} , I _C = 250μA (25°C - 150°C)
g _{fe}	Forward Transconductance	—	30	—	S	V _{CE} = 50V, I _C = 33A, PW = 20μs
I _{CES}	Collector-to-Emitter Leakage Current	—	—	250	μA	V _{GE} = 0V, V _{CE} = 1200V, T _J = 25°C
		—	—	1000		V _{GE} = 0V, V _{CE} = 1200V, T _J = 150°C
I _{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V _{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q _g	Total Gate Charge (turn-on)	—	151	227	nC	I _C = 33A
Q _{ge}	Gate-to-Emitter Charge (turn-on)	—	26	39		V _{GE} = 15V
Q _{gc}	Gate-to-Collector Charge (turn-on)	—	62	93		V _{CC} = 600V
E _{off}	Turn-Off Switching Loss	—	15	16	mJ	I _C = 33A, V _{CC} = 600V, V _{GE} = 15V R _G = 5Ω, L = 400μH, T _J = 25°C Energy losses include tail
t _{d(off)}	Turn-Off delay time	—	485	616	ns	I _C = 33A, V _{CC} = 600V, V _{GE} = 15V
t _f	Fall time	—	1193	1371		R _G = 5Ω, L = 400μH, T _J = 25°C
E _{off}	Turn-Off Switching Loss	—	29	—	mJ	I _C = 33A, V _{CC} = 600V, V _{GE} = 15V R _G = 5Ω, L = 400μH, T _J = 150°C Energy losses include tail
t _{d(off)}	Turn-Off delay time	—	689	—	ns	I _C = 33A, V _{CC} = 600V, V _{GE} = 15V
t _f	Fall time	—	2462	—		R _G = 5Ω, L = 400μH, T _J = 150°C
C _{ies}	Input Capacitance	—	3804	—	pF	V _{GE} = 0V
C _{oes}	Output Capacitance	—	161	—		V _{CC} = 30V
C _{res}	Reverse Transfer Capacitance	—	31	—		f = 1.0Mhz
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				T _J = 150°C, I _C = 99A V _{CC} = 960V, V _p ≤ 1200V R _G = 5Ω, V _{GE} = +20V to 0V

Notes:

- ① V_{CC} = 80% (V_{CES}), V_{GE} = 20V, L = 400μH, R_G = 50Ω.
- ② Pulse width limited by max. junction temperature.
- ③ Refer to AN-1086 for guidelines for measuring V_{(BR)CES} safely.
- ④ R_θ is measured at T_J of approximately 90°C.
- ⑤ Calculated continuous current based on maximum allowable junction temperature. Bond wire current limit is 78A. Note that current limitations arising from heating of the device leads may occur with some lead mounting arrangements.

Qualification Information[†]

Qualification Level		Automotive (per AEC-Q101) ^{††}	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		3L-Super-TO-220	N/A
ESD	Machine Model	Class M4 (+/- 800 V) (per AEC-Q101-002)	
	Human Body Model	Class H3A (+/- 6000V) (per AEC-Q101-001)	
	Charged Device Model	Class C5 (+/- 2000 V) (per AEC-Q101-005)	
RoHS Compliant		Yes	

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/>

†† Highest passing voltage.

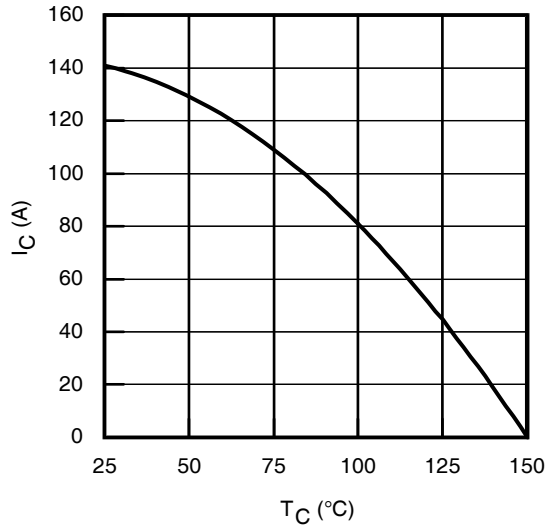


Fig. 1 - Maximum DC Collector Current vs. Case Temperature

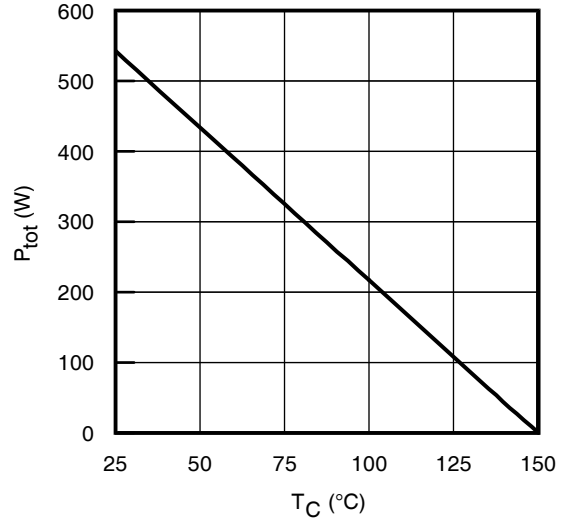


Fig. 2 - Power Dissipation vs. Case Temperature

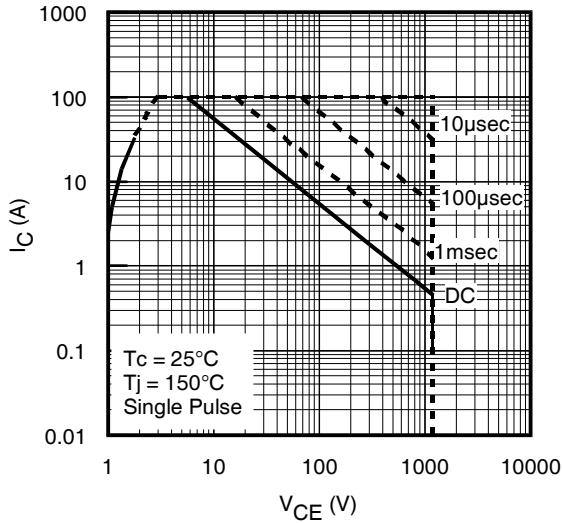


Fig. 3 - Forward SOA
 $T_C = 25^\circ\text{C}$, $T_J \leq 150^\circ\text{C}$; $V_{GE} = 15\text{V}$

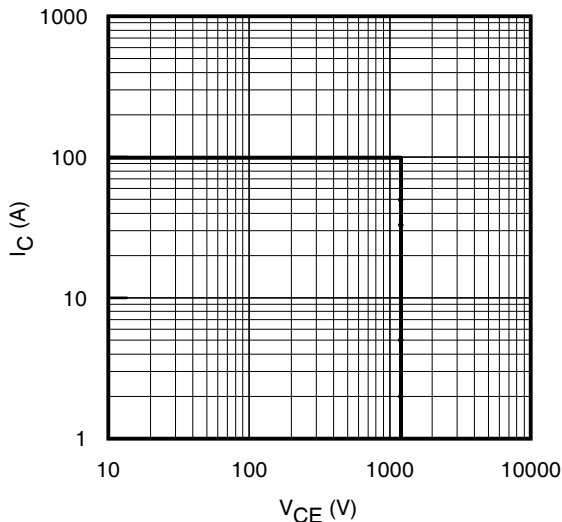


Fig. 5- Reverse Bias SOA
 $T_J = 150^\circ\text{C}$; $V_{GE} = 20\text{V}$

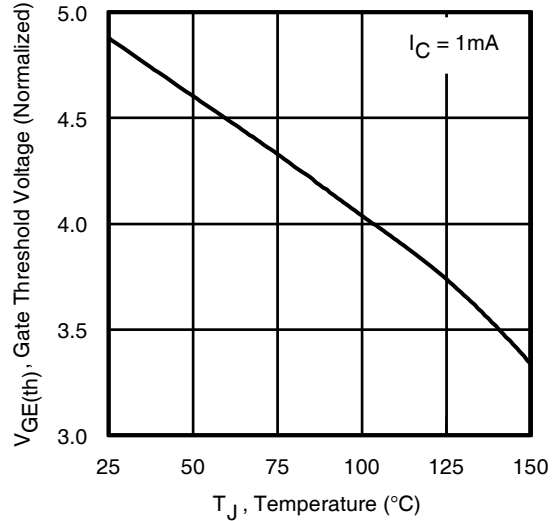


Fig. 4 - Typical Gate Threshold Voltage (Normalized) vs. Junction Temperature

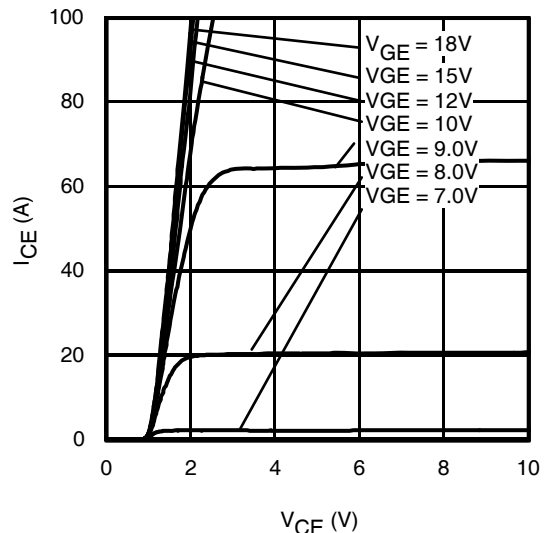


Fig. 6 - Typ. IGBT Output Characteristics
 $T_J = -40^\circ\text{C}$; $t_p = 20\mu\text{s}$

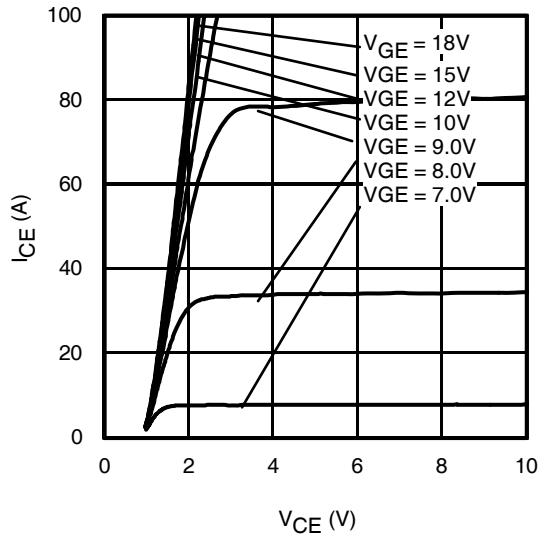


Fig. 7 - Typ. IGBT Output Characteristics
 $T_J = 25^\circ\text{C}$; $t_p = 20\mu\text{s}$

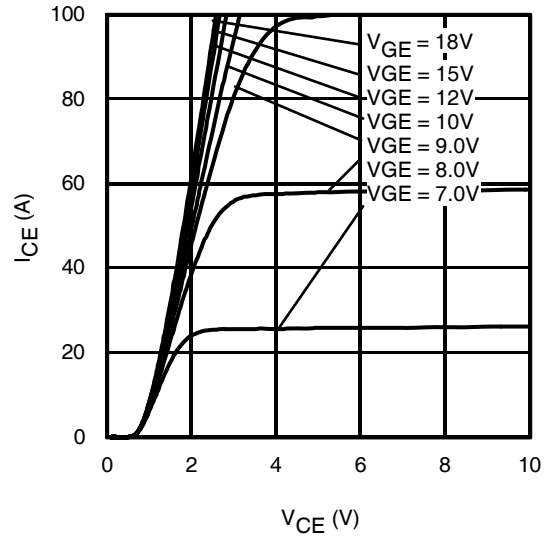


Fig. 8 - Typ. IGBT Output Characteristics
 $T_J = 150^\circ\text{C}$; $t_p = 20\mu\text{s}$

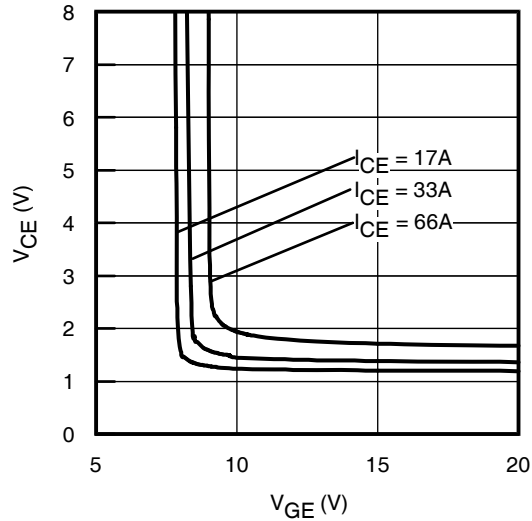


Fig. 9 - Typical V_{CE} vs. V_{GE}
 $T_J = -40^\circ\text{C}$

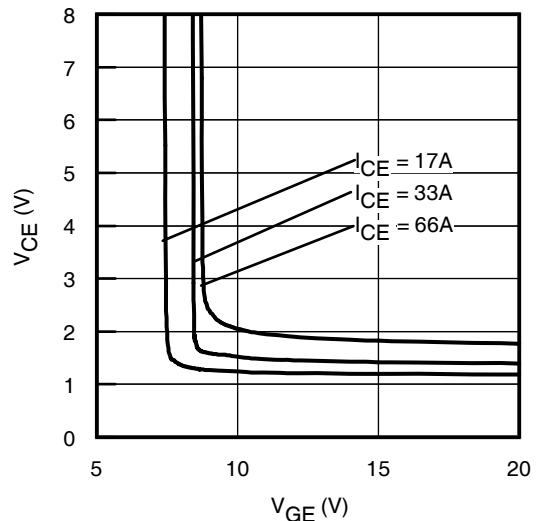


Fig. 10 - Typical V_{CE} vs. V_{GE}
 $T_J = 25^\circ\text{C}$

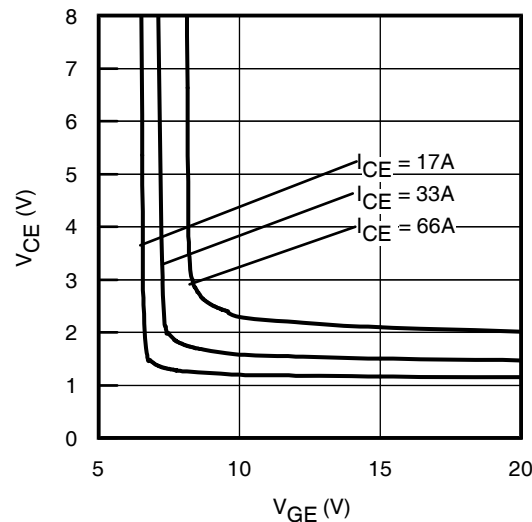


Fig. 11 - Typical V_{CE} vs. V_{GE}
 $T_J = 150^\circ\text{C}$

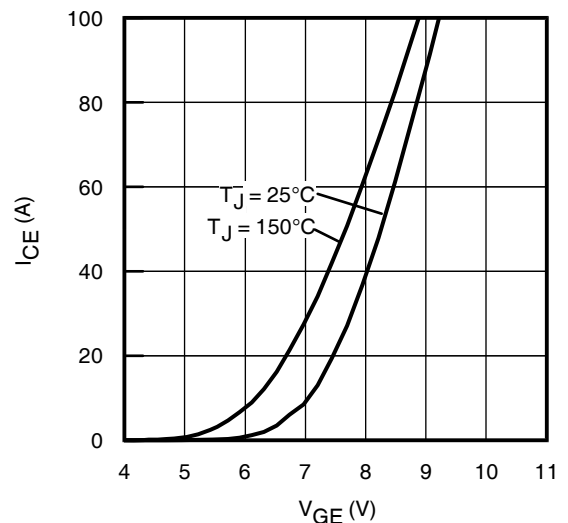
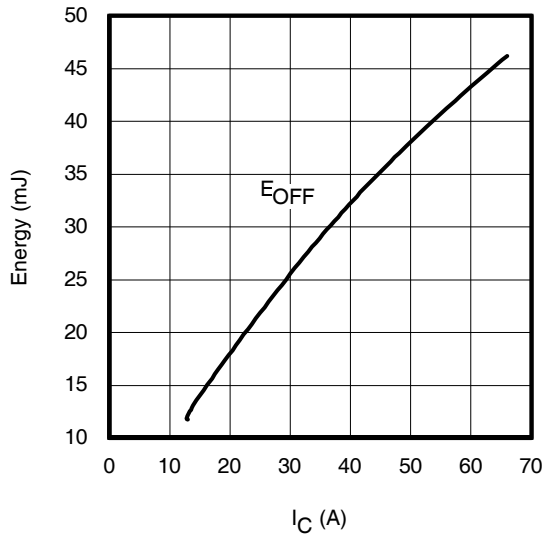
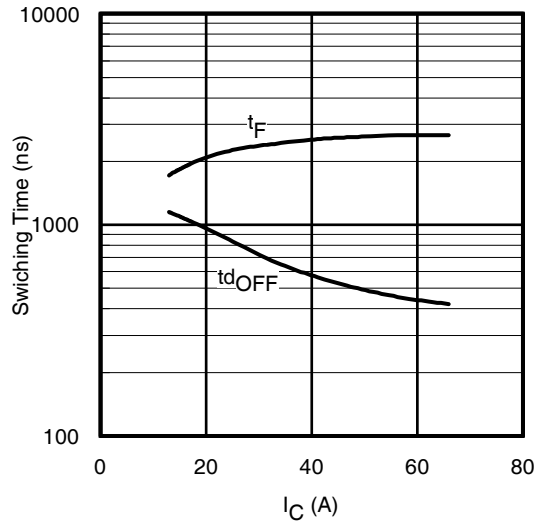
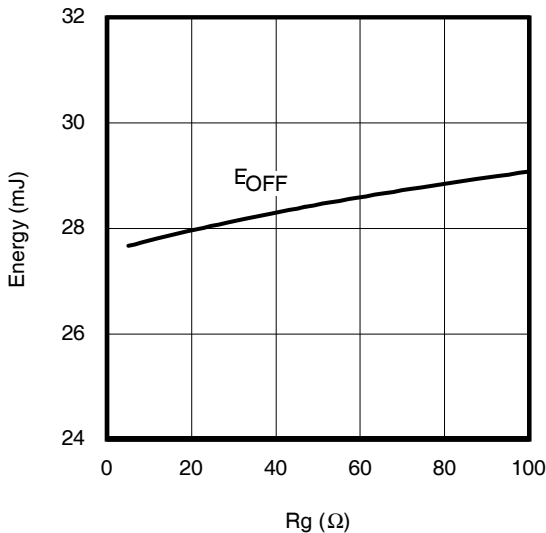
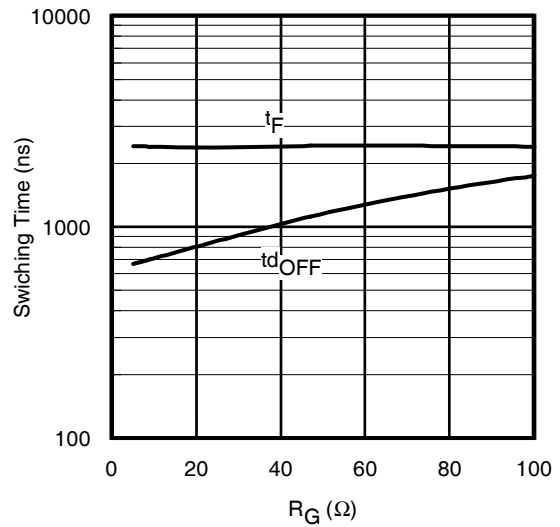
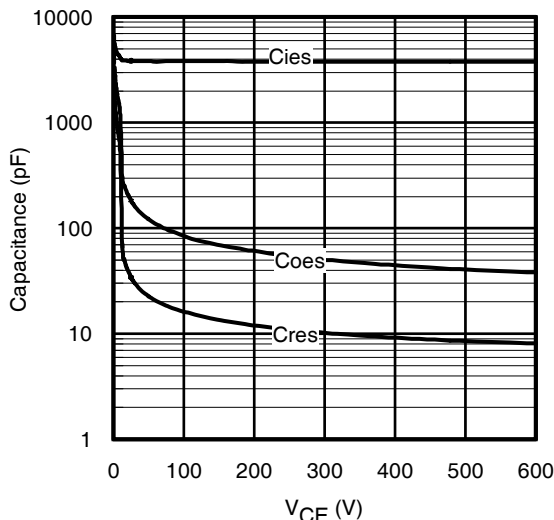
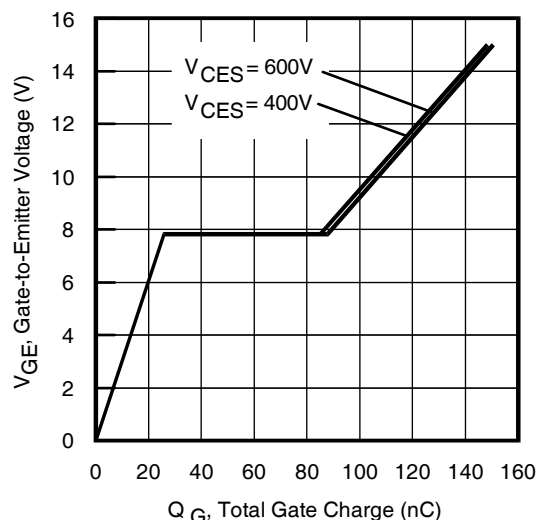


Fig. 12- Typ. Transfer Characteristics
 $V_{CE} = 50\text{V}$; $t_p = 20\mu\text{s}$


Fig. 13 - Typ. Energy Loss vs. I_C
 $T_J = 150^\circ\text{C}; L = 400\mu\text{H}; V_{CE} = 600\text{V}, R_G = 5\Omega; V_{GE} = 15\text{V}$

Fig. 14 - Typ. Switching Time vs. I_C
 $T_J = 150^\circ\text{C}; L = 400\mu\text{H}; V_{CE} = 600\text{V}, R_G = 5\Omega; V_{GE} = 15\text{V}$

Fig. 15 - Typ. Energy Loss vs. R_G
 $T_J = 150^\circ\text{C}; L = 400\mu\text{H}; V_{CE} = 600\text{V}, I_{CE} = 33\text{A}; V_{GE} = 15\text{V}$

Fig. 16 - Typ. Switching Time vs. R_G
 $T_J = 150^\circ\text{C}; L = 400\mu\text{H}; V_{CE} = 600\text{V}, I_{CE} = 33\text{A}; V_{GE} = 15\text{V}$

Fig. 17 - Typ. Capacitance vs. V_{CE}
 $V_{GE} = 0\text{V}; f = 1\text{MHz}$

Fig. 18 - Typical Gate Charge vs. V_{GE}
 $I_{CE} = 33\text{A}; L = 2.0\text{mH}$

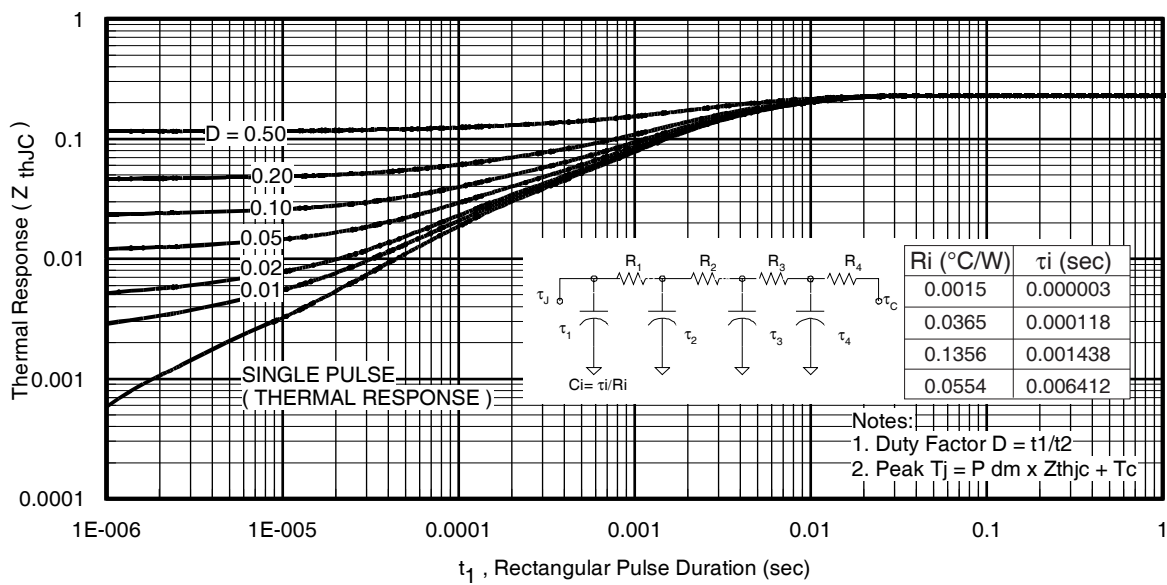


Fig 19. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

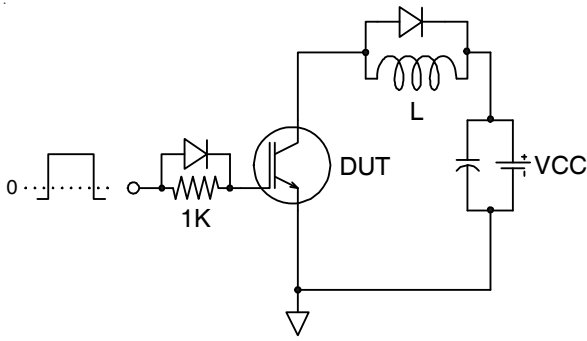


Fig.C.T.1 - Gate Charge Circuit (turn-off)

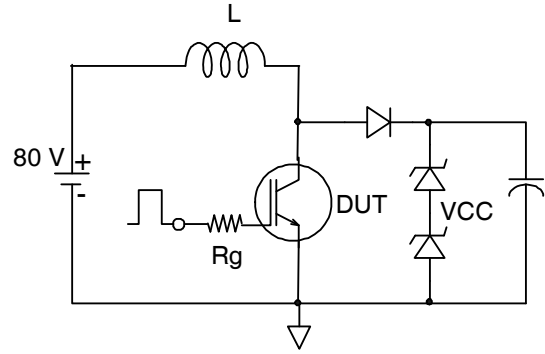


Fig.C.T.2 - RBSOA Circuit

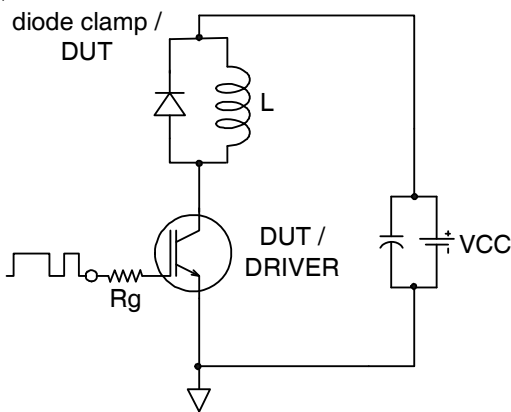


Fig.C.T.3 - Switching Loss Circuit

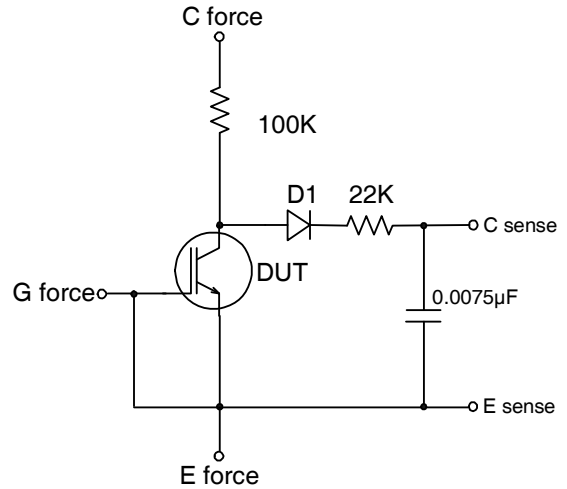


Fig.C.T.4 - BVCES Filter Circuit

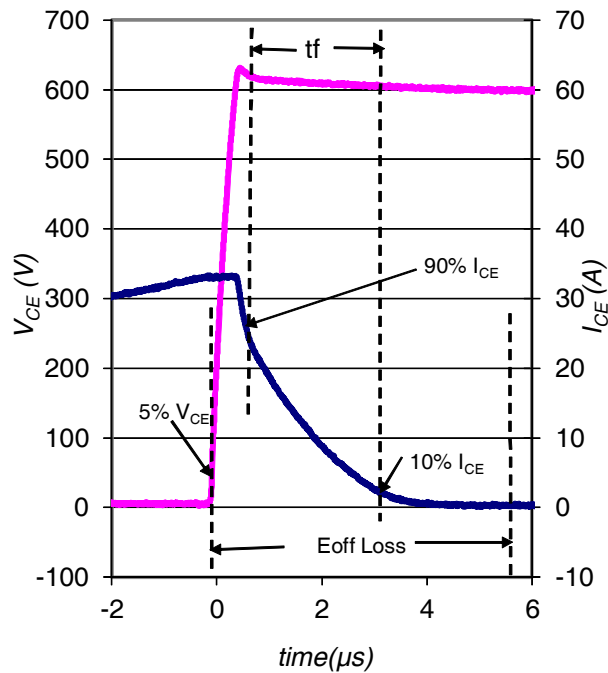
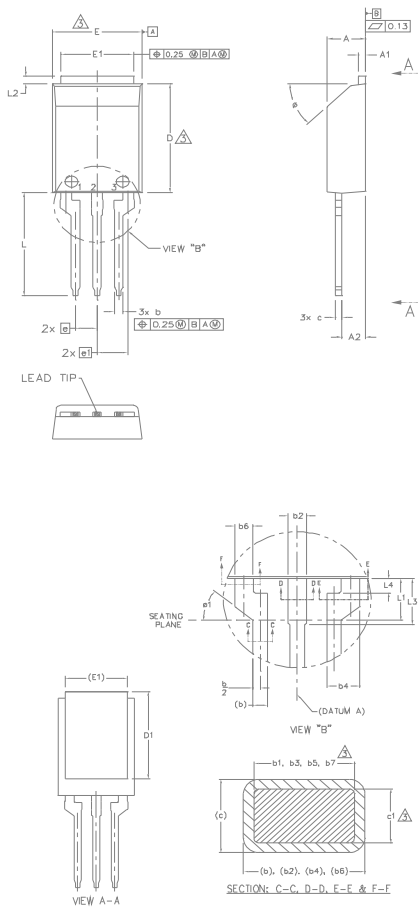


Fig. WF1 - Typ. Turn-off Loss Waveform
@ $T_J = 150^\circ\text{C}$ using Fig. CT.3

Super-TO-220 Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M-1994
2. DIMENSIONS b1, b3, b5 & c1 APPLY TO BASE METAL ONLY.
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [0.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTER EXTREMES OF THE PLASTIC BODY.
4. ALL DIMENSIONS SHOWN IN MILLIMETERS.
5. CONTROLLING DIMENSION: MILLIMETER.
6. OUTLINE CONFORMS TO JEDEC OUTLINE TO-273AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.34	4.74	.171	.187	
A1	0.50	1.00	.020	.039	
A2	2.50	3.00	.098	.118	
b	0.90	1.30	.035	.051	
b1	0.80	1.10	.031	.043	2
b2	1.25	1.65	.049	.065	
b3	1.10	1.55	.043	.061	2
b4	2.35	2.55	.093	.100	
b5	2.30	2.50	.091	.098	2
b6	1.25	1.65	.049	.065	
b7	1.10	1.55	.043	.061	2
c	0.70	1.00	.028	.039	
c1	0.60	0.90	.024	.035	2
D	14.00	15.00	.0551	.591	3
D1	12.50	13.50	.492	.531	
E	10.00	11.00	.394	.433	3
E1	8.00	9.00	.315	.354	
e	2.55 BSC		.100 BSC		
e1	3.66 BSC		.144 BSC		
L	13.00	14.50	.512	.571	
L1	3.00	3.50	.118	.138	
L2	0.50	1.50	.020	.059	
L3	3.50	4.00	.138	.157	
L4	-	1.50	-	.059	
phi	42.5*	47.5*	42.5*	47.5*	
phi1	-	42.5*	-	42.5*	

LEAD ASSIGNMENTS

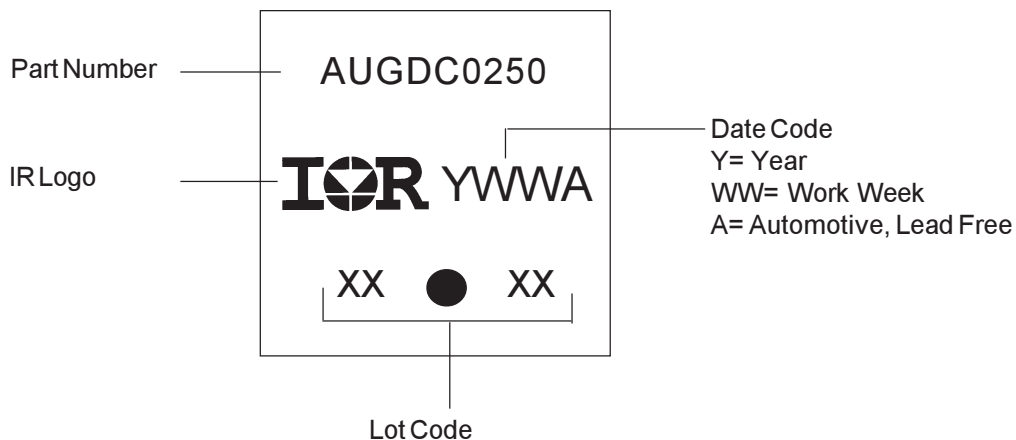
MOSFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBT

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

Super-TO-220 Part Marking Information



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

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<http://www.irf.com/technical-info/>

WORLD HEADQUARTERS:

101 N. Sepulveda Blvd., El Segundo, California 90245

Tel: (310) 252-7105

Revision History

Date	Comments
9/2/2014	<ul style="list-style-type: none"> • Updated datasheet with IR corporate template. • Removed Ic Nominal current on page 1. • Updated package outline on page 9. • Updated typo on switch time test condition from "25C" to "150C" on page 2.
12/1/2014	<ul style="list-style-type: none"> • Updated Bvdss test condition from "100uA" to "250uA" on page 2. • Updated Vgeth test condition from "1mA" to "250uA" on page 2. • Updated Vgeth temp coefficient test condition from "1mA" to "250uA" and spec from "-12mV/C" to "-15mV/C" on page 2.
3/2/2015	<ul style="list-style-type: none"> • Removed I_{CES} = 2uA @ VCE = 10V on page 2.